Preliminary



SANYO Semiconductors DATA SHEET

STK760-221A-E Thick-Film Hybrid IC Single-phase Rectification PFC Hybrid IC

Overview

The STK760-221A-E is an average current control type hybrid IC that integrates in a single package the power stages for the step-up active converter and the control IC, and overcurrent/overvoltage protection circuits. It is designed to improve the power factor of single-phase AC power supplies.

Applications

• Power rectification for air conditioners and general-purpose inverters as a single-phase rectification active converter.

Features

- IGBT switching power device employed in the active converter output stage.
- On-chip regulator for PFC control supports a wide range of input voltage (up to 50V).
- Full complement of protection circuits, including overcurrent, overvoltage, and undervoltage protection, plus soft start function.
- Logic level PFC controlled ON/OFF control.
- On-chip light-load correction circuit that minimizes output voltage increase when no load is applied.
- SIP package providing a high degree freedom for mounting the IC in the set.

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Specifications

Absolute maximum ratings at Tc = 25°C

Parameter		Symbol	Conditions	Ratings	unit	
IGBT			VCES		600	V
(TR2+TR3)	Repetitive peak collector current		ICP	*1	180	Α
	Collector current		IC		70	Α
	Allowable pov	Allowable power dissipation			166	W
FRD	Diode reverse	e voltage	VRM		600	V
(D2)	Repetitive pe	ak forward current	IF2P	*1	160	Α
	Forward Curr	ent	IF2		41	Α
	Allowable pov	wer dissipation	Pd		73	W
FRD	Repetitive pe	ak forward current	IFP	*1	15	Α
(D3)	Forward curre	ent	IF3		7	Α
	Allowable pov	wer dissipation	Pd		13	W
Supply voltage (P	Pin 1)		Vs		21 to 50	V
Supply current (P	in 1)		Isc		60	mA
Signal pin input v	oltage	Pin 5	VVDET			
Pin 12 Pin 13		VEI]	-0.3 to 5.0	V	
		VOVP				
		Pin 9	VIS		-10 to 5.0	V
	Pin 4		VONF		-0.3 to V _{CC}	V
Oscillation freque	ncy		fosc		40	kHz
Maximum AC inp	ut voltage		VAC	Single-phase full-wave rectification waveform voltage	264	٧
Maximum output voltage		VO	Under the operating conditions of the application circuit 45		٧	
Input current (in steady state)		IN	Under the operating conditions of the application circuit.		Arms	
Load power			Wo	VAC=200V		kW
Chip junction temperature			Tj		150	°C
Operating case temperature		Tc	Center of the resin package on the reverse side *2 -20 to +10		°C	
Storage temperature		Tstg	-40 to +12		°C	
Tightening torque				M4 screws *3	1.17	N • m
Dielectric strength voltage			VINS	Sine wave, 50Hz, AC 1 minute *4	2000	VRMS

^{*1.} Repetitive peak current with the duty ratio of D=0.1 and tp=1ms.

Electrical Characteristics at Tc=25°C, Vs=21V with the designated circuit

(Apply V_{CC}=18.0V directly to pin 2 unless Vs input is specified.)

(Apply V _C C=18.0V directly to pin 2 unless Vs input is specified.)							
Parameter	Symbol	Conditions	min	typ	max	unit	Test circuit
Power output block							
Collector-to-emitter cutoff current (TR2+TR3)	ICES	V _{CE} =600V			200	μА	Fig.1
Collector-to-emitter saturation voltage (TR2+TR3)	V _{CE} (sat)	V _{CC} =18.0V, I _C =40A		1.9	2.4	٧	Fig.2
Diode reverse voltage (D2)	IR	V _R =600V			100	μΑ	Fig.1
Diode forward voltage (D2)	V _F	I _F =40A		2.1	2.6	V	Fig.3
Diode forward voltage (D3)	٧ _F	I _F =5A		2.5	3.5	V	Fig.3
Junction-to-case thermal resistance	θј-с1	IGBT (TR2+TR3)		0.75		°C /W	
	θј-с2	FRD (D2)		1.7		°C /W	
	θј-с3	FRD (D3)		9.0		°C /W	

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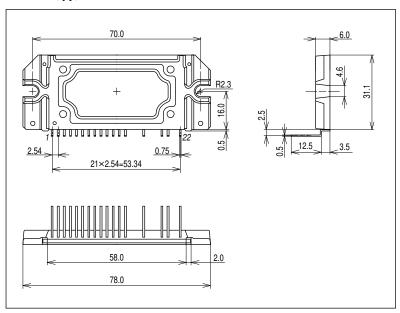
^{*2.} The measurement point must be within 10 millimeters square wide in the center of the resin package on the reverse side.

^{*3.} The tightening torque must be within the range of 0.79 to 1.17N • m. The flatness of the heat sink to be connected must be 0.15mm or less.

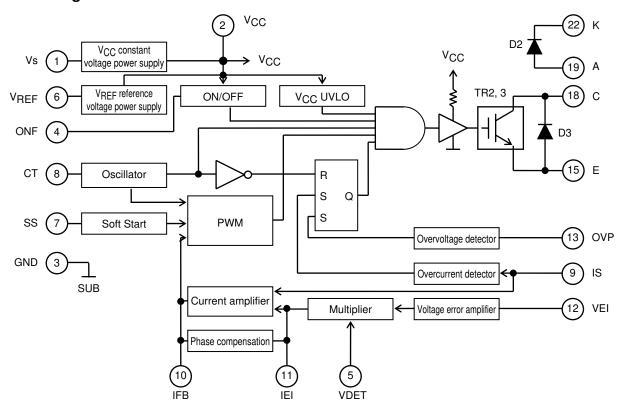
^{*4.} Test conditions: AC 2500V for 1 second.

Parameter	Symbol	Conditions	min	typ	max	unit	Test circuit	
V _{CC} regulator block	•							
V _{CC} regulator output voltage	V _{CC}	Vs=21V, I _{CC} OUT=0 to 40mA	17.9	18.7	19.6	٧	Fig.4	
Control IC block								
Control circuit current dissipation	I _{CC} (ON)	V _{CC} =18.0V, ONF=5V		7	11	mA		
	I _{CC} (OFF)	V _{CC} =18.0V, ONF=0V		0.06	0.5	mA	Fig.5	
Reference voltage	V _{REF}	V _{CC} =18.0V, ONF=5V	4.75	5.0	5.25	V		
Oscillation frequency	fosc	V _{CC} =18.0V, ONF=5V	19.3	21.5	23.7	kHz	Fig.5	
Overcurrent protection input threshold voltage	VTHOCP	V _{CC} =18.0V, ONF=5V	-1.20	-1.10	-1.00	٧	Fig.6	
Voltage error amplifier reference voltage	Vr	V _{CC} =18.0V, ONF=5V	1.509	1.55	1.591	V		
OVP threshold voltage	VTHOVP	V _{CC} =18.0V, ONF=5V	1.607	1.64	1.673	V	F: 7	
SS charge current	ICHG	V _{CC} =18.0V, ONF=5V		11		μΑ	Fig.7	
SS input threshold voltage	VTHSSO	Duty cycle=0%		0.34		V		
	VTHSSM	Duty cycle=D _{MAX}		3.4		٧		
ON/OFF threshold voltage	VTHON	V _{CC} =18.0V	3.5	3.95	4.4	٧	Fig.8	
	VTHOFF	V _{CC} =18.0V	2.4	2.8	3.2	>		
Startup V _{CC} voltage	VTHUON	ONF=5V	15.5	16.5	17.5	٧	F: 0	
Shutdown V _{CC} voltage	VTHUOFF	ONF=5V	8.2	8.9	9.6	٧	Fig.9	
Power output block								
Switching time	tON	I _C =30A, Inductive load	0.2	0.35	0.8	μs		
	tOFF			0.85	1.4	μs	Fi~ 10	
	t _{rr}			0.04		μs	Fig.10	
Diode recovery current (D2)	I _{rr}			20		Α		
Application circuit operation: Set to VAC=20	00V, and V _O =380	V						
Power factor	cosφ	Wo=400W	0.9	0.95		_	Fig.11	
		Wo=2kW	0.98	0.99	1.0	•		

Package Dimensions unit:mm (typ)



Block Diagram



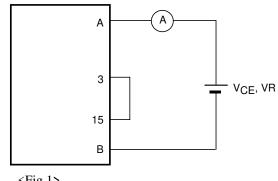
Pin Functions

Pin No.	Pin Name	Description
1	Vs	Operating supply voltage (+18V Reg. input)
2	V _{CC}	+18V V _{CC} power supply output
3	GND	GND pin
4	ONF	ON/OFF control pin
5	VDET	Multiplication input
6	V _{REF}	+5V reference voltage output
7	SS	Soft start pin
8	СТ	Operating frequency setting pin
9	IS	Current detection signal
10	IFB	Phase compensation (current amplification output)
11	IEI	Current amplification input
12	VEI	Output voltage control input
13	OVP	Overvoltage limiting
14	-	No connection
15	E	TR2, 3 (IGBT) emitter
16, 17	-	No connection
18	С	TR2, 3 (IGBT) collector
19	A	D2 (FRD) anode
20, 21	-	No connection
22	К	D2 (FRD) cathode

Test Circuit

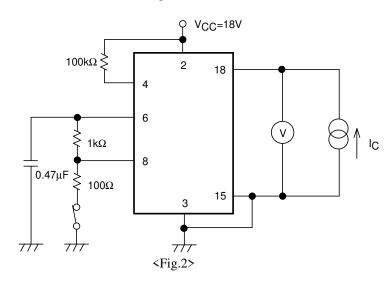
1: IR, ICES

	TR1	D2
Α	18	22
В	15	19



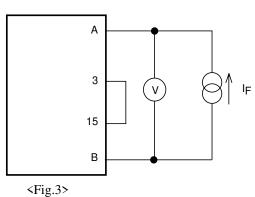
<Fig.1>

2: V_{CE}(sat) (Test by pulse)

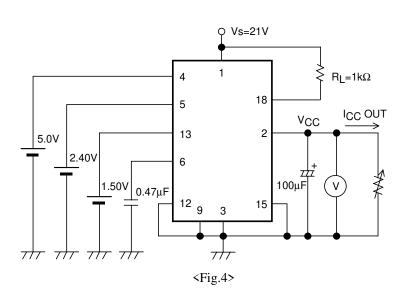


3: V_F (Test by pulse)

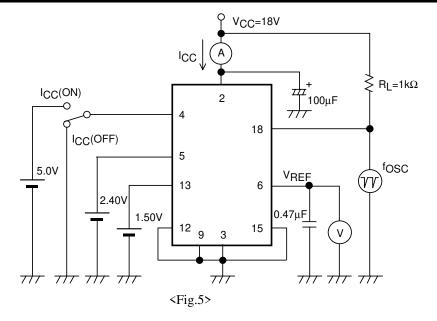
	D2	D3
Α	19	15
В	22	18



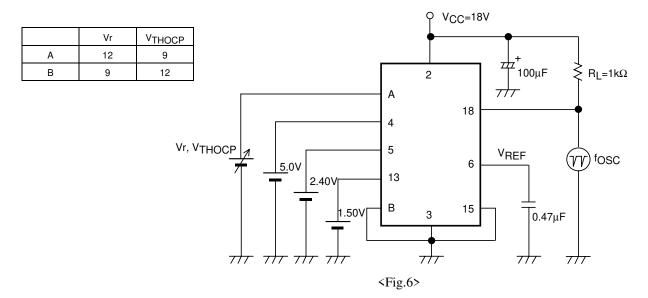
4: V_{CC} (V_{CC}-Reg.OUT)



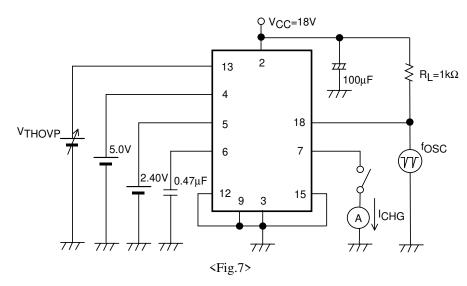
5: ICC(ON)/ICC(OFF), VREF, fOSC



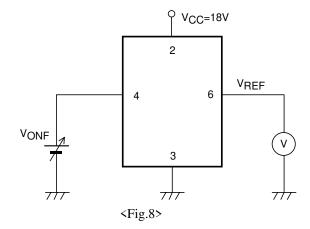
6: Vr, VTHOCP



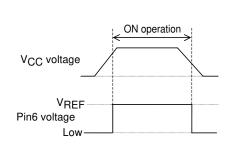
7: VTHOVP, ICHG

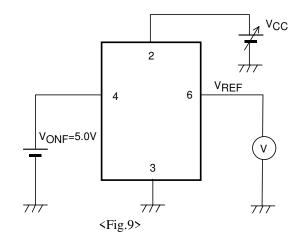


8: V_{THON}, V_{THOFF}

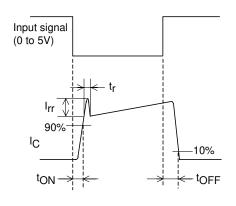


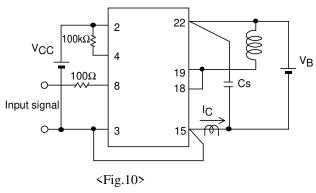
9: VTHUON, VTHUOFF



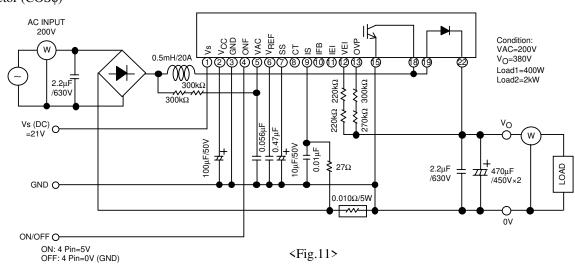


10: ton, toff, trr, Irr

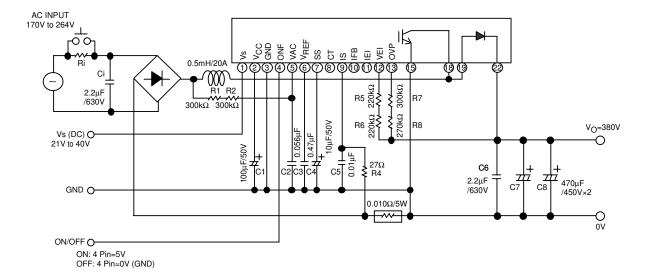




11: Power factor (COS\$\phi\$)



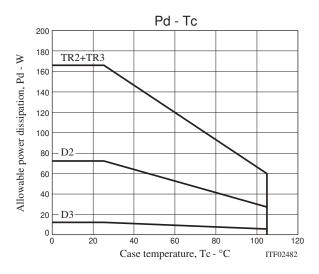
Sample Application Circuit



* When using the IC in a system having an input power voltage of 200V, insert a rush current limiting circuit, which consists of a limiting resistor Ri and a switch, to prevent the internal diodes from being damaged by the charging current from the output capacitor

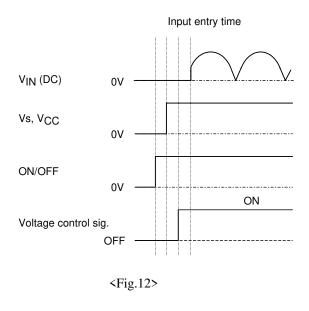
Recommended conditions

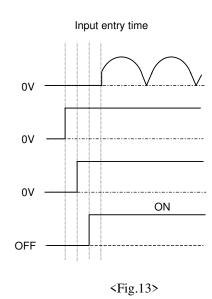
Parameter	Symbol	Conditions	Recommended values	unit
Commercial AC voltage	VAC	50/60Hz	170 to 264	Vrms
Output voltage	V _O		VAC×√2+(10 to 15)≤ 450	V
Output overvoltage detection voltage	V _{OV}		V _{OUT} +(10 to 20)	V
Supply voltage (Pin 1)	Vs		21 to 40	V



Timing Charts

The IC will never be subjected to fatal damage when a power supply input or signals are applied or are not applied at any timing. If the V_{IN} (DC) input is applied to the IC at the timing shown in Figure 12 or 13, however, since the soft start circuit is inactive in this case, it is likely that the overcurrent protection circuit is activated and audible tone is generated out of the coil. To avoid this area of timing, it is necessary that the ON/OFF or V_{CC} input be applied after V_{IN} (DC).





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